









	<h2 style="color: red;">IPD60R1K4C6</h2>	
	Hersteller-Teilenummer:	IPD60R1K4C6
	Hersteller / Marke:	International Rectifier (Infineon Technologies)
	Teil der Beschreibung:	MOSFET N-CH 600V 3.2A TO252-3
Datenblätter:	 IPD60R1K4C6.pdf	
RoHs Status:	Bleifrei / RoHS-konform	
Lagerzustand:	New original, 19454 pcs Stock Available.	
Liefern von:	Hong Kong	
Versandweg:	DHL/Fedex/TNT/UPS/EMS	
<p>Image may be representation. See specs for product details.</p>		

Spezifikationen

Teilenummer	IPD60R1K4C6
Hersteller	International Rectifier (Infineon Technologies)
Beschreibung	MOSFET N-CH 600V 3.2A TO252-3
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	19454 pcs Stock
Serie	CoolMOS™
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-252-3, DPak (2 Leads + Tab), SC-63
Supplier Device-Gehäuse	PG-TO252-3
Verlustleistung (max)	28.4W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	600V
Strom - Ununterbrochener Abfluss (Id) bei 25 °C	3.2A (Tc)
Rds On (Max) @ Id, Vgs	1.4 Ohm @ 1.1A, 10V
VGS (th) (Max) @ Id	3.5V @ 90µA
Gate Charge (Qg) (Max) @ Vgs	9.4nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	200pF @ 100V
Verpackung	Original-Reel®

IPD60R1K4C6 ist neu im Original, Suche IPD60R1K4C6 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie IPD60R1K4C6 International Rectifier (Infineon Technologies) mit Garantie und Vertrauen. Anfrage IPD60R1K4C6: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>IPD60R180P7SAUMA1 International Rectifier (Infineon Technologies) MOSFET N-CH 600V 18A TO252-3</p>	 <p>IPD60R180P7ATMA1 International Rectifier (Infineon Technologies) MOSFET N-CH 650V 18A TO252-3</p>	 <p>IPD60R1K0CEAUMA1 International Rectifier (Infineon Technologies) CONSUMER</p>	 <p>IPD60R1K4C6ATMA1 International Rectifier (Infineon Technologies) MOSFET N-CH 600V 3.2A TO252-3</p>
 <p>IPD60R1K0CE INFINEO IPD60R1K0CE INFINEO</p>	 <p>IPD60R1K5CEATMA1 International Rectifier (Infineon Technologies) MOSFET N-CH 600V TO-252-3</p>	 <p>IPD60R1K5CEAUMA1 International Rectifier (Infineon Technologies) MOSFET N-CH 650V 5A TO252</p>	 <p>IPD60R1K0CEATMA1 International Rectifier (Infineon Technologies) MOSFET N-CH 600V TO-252-3</p>

heiße Teile

Mehr

IPD50N06S3L-06	IPD50N06S3L-08	IPD50N06S3L-13	IPD50N06S4-09	IPD50N06S4-12
IPD50N06S4L-08	IPD50N06S4L-12	IPD50N10S3L-16	IPD50P03P4L-04	IPD50P03P4L-11
IPD50P04P4-13	IPD50P04P4L-11	IPD50R280CE	IPD50R380CE	IPD50R399CP
IPD50R500CE	IPD50R520CP	IPD50R650CE	IPD50R950CE	IPD530N15N3
IPD530N15N3G	IPD530N15NG	IPD600N25N3G	IPD60N10S4L-12	IPD60R1K0CE
IPD60R1K5CE	IPD60R2K0C6	IPD60R360P	IPD60R380C6	IPD60R380E6
IPD60R380P6	IPD60R385CP	IPD60R3K3C6	IPD60R400CE	IPD60R450E6
IPD60R520C6	IPD60R520CP	IPD60R600C6	IPD60R600CP	IPD60R600E6
IPD60R600P6	IPD60R750E6	IPD60R800CE	IPD60R950C6	IPD640N06LG
IPD64CN10NG	IPD65R1K4C6	IPD65R250C6	IPD65R250E6	IPD65R380C6

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